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Cypress Semiconductor Product Qualification Plan

QTP# 082703 VERSION*A
January 2015

8Meg nvSRAM Product Family S8TNV-5, Fab 4	
CY14B108L CY14B108N	8 Mbit (1024K x 8/512K x 16) nvSRAM
CY14B108K CY14B108M	8 Mbit (1024K X 8/512K X 16) nvSRAM with real time clock

FOR ANY QUESTIONS ON THIS REPORT, PLEASE CONTACT
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QUALIFICATION HISTORY

Qual Report		Description of Qualification Purpose		Date Comp
071304		To qualify S8 SONOS technology and 4M nvSRAM devices CY14B104L / CY14B104N (7C14104AC base die) using S8TNV-5R, fabricated at Cypress Minnesota CMI (Fab4)		Nov 2008
082704		To qualify 4M nvSRAM Evans (<i>with both RTC-Real Time Clock and bond options for Non-RTC</i>) devices CY14B104*/CY14B102*/CY14E104* (7C14104CC base die) using S8TNV-5R, fabricated at Cypress Minnesota CMI (Fab4)		July 2009
092804		1 Million Endurance Qualification for 4 Meg Evans nvSRAM		Nov 2009
082703		To qualify 8M nvSRAM (two 4M stack dice) devices (CY14B108*) using S8TNV-5 Technology, Fab 4		Nov 2009

PRODUCT DESCRIPTION (S8TNV-5)	
Qualification Purpose:	Qualify 8M nvSRAM (two 4M stack dice) devices (CY14B108*) using S8TNV-5 Technology, Fab 4
Marketing Part #:	CY14B108L, CY14B108N, CY14B108K, CY14B108M
Device Description:	3V & 5V Commercial/Industrial, available in 44-Lead TSOP II / 54-Lead TSOP II / 48 BGA
Cypress Division:	Cypress Semiconductor Corporation – Memory Product Division

TECHNOLOGY/FAB PROCESS DESCRIPTION			
Number of Metal Layers:	3	Metal Composition:	Metal 1: 300Å TiW / 3,200Å Al / 100Å Ti Metal 2: 300Å TiW / 3,200Å Al / 100Å Ti Metal 3: 300Å TiW / 8,000Å Al / 150Å Ti
Passivation Type and Materials:	Si ₂ N ₃ 7000Å & SiO ₂ 700Å		
Generic Process Technology/Design Rule (□-drawn):	S8TNV-5R/0.13µm		
Gate Oxide Material/Thickness (MOS):	37Å (LV) & 110Å (HV)		
Name/Location of Die Fab (prime) Facility:	Cypress Semiconductor -- Bloomington, MN		
Die Fab Line ID/Wafer Process ID:	Fab4 / S8TNV-5		

PACKAGE AVAILABILITY

PACKAGE	ASSEMBLY FACILITY SITE
44-Lead TSOPII	ASE-TAIWAN
54-Lead TSOPII	ASE-TAIWAN
48 FBGA	ASE-TAIWAN

Note: Package Qualification details available upon request.

MAJOR PACKAGE INFORMATION USED IN THIS QUALIFICATION

Package Designation:	ZW44
Package Outline, Type, or Name:	44-Lead Thin Shrink Outline Package (Stacked Die)
Mold Compound Name/Manufacturer:	HITACHI CEL9200THF
Mold Compound Flammability Rating:	V-O per UL94
Oxygen Rating Index: >28%	NA
Lead Frame Material:	Copper
Lead Finish, Composition / Thickness:	Pure Sn (100%)
Die Backside Preparation Method/Metallization:	Backgrind
Die Separation Method:	100% Saw
Die Attach Supplier:	Hitachi
Die Attach Material:	FH-900 Tape Film
Die Attach Method:	Film
Bond Diagram Designation:	001-52423
Wire Bond Method:	Thermosonic
Wire Material/Size:	Au / 1.0 mil
Thermal Resistance Theta JA °C/W :	152°C/W
Package Cross Section Yes/No:	NO
Assembly Process Flow:	49-41999
Name/Location of Assembly (prime) facility:	ASE - Taiwan
MSL Level:	3
Reflow Profile:	260C

ELECTRICAL TEST / FINISH DESCRIPTION

Test Location:	CML-R
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Note: Package Qualification details upon request

RELIABILITY TESTS PERFORMED PER SPECIFICATION REQUIREMENT

Stress/Test	Test Condition (Temp/Bias)	Result P/F
High Temperature Operating Life Early Failure Rate (EFR)	Dynamic Operating Condition, 150°C, 2.7V, 48 Hours JESD22-A-108-B	P
High Temperature Operating Life Latent Failure Rate (LFR)	Dynamic Operating Condition, 150°C, 2.7V, 500 Hours JESD22-A-108-B	P
Pre/Post LFR AC/DC Char	AC/DC Critical Parameter Char at LFR 0hrs, 80hrs & 500hrs	P
Endurance	200K Cycles @ 90C, Per datasheet	P
Endurance	1M Cycles @ 24C and 90C	P
Data Retention	150°C, 1000 Hours	P
Temperature Cycle	-65°C to 150°C, JESD22-A-104 500 Cycles, Require Precondition	P
High Accelerated Saturation Test (HAST)	130°C, 3.63V, 85%RH, JESD22-A-110-B 128 Hours, Require Precondition	P
Pressure Cooker	121°C/100%RH, JESD22-A102-C 168 Hours, Require Precondition	P
Precondition	JESD22 Moisture Sensitivity	P
Electrostatic Discharge Human Body Model (ESD-HBM)	2,200V, JESD22-A114E	P
Electrostatic Discharge Charge Device Model (ESD-CDM)	500V, JESD22-C101C	P
Electrostatic Discharge Machine Model (ESD-MM)	200V, JESD22-A115-A	P
Latch-up Sensitivity	5.4V,± 200mA, 125°C, EIA/JESD78	P
Age Bond Strength	Mil-Std-883, Method 2011	P
Acoustic (M3)	J-STD-020	P
Soft Error (Alpha Particle)	JESD89A	P
Soft Error (Neutron/Proton)	JESD89A	P
SEM X-Section	XY audit at center wafer and edge wafer	P
Low Temperature Operating Life Test	Dynamic Operating Condition, 2.7V, -30°C, 500 Hours	P
High Temp Steady State Life Test	Static Operating Condition, 2.7V, 150°C, 1000 Hours	P

RELIABILITY FAILURE RATE SUMMARY

Stress/Test	Device Tested/ Device Hours	# Fails	Activation Energy	Thermal AF ⁴	Failure Rate
High Temperature Operating Life Early Failure Rate	1,557 Devices	0	N/A	N/A	0 PPM
High Temperature Operating Life ^{1,2} , Long Term Failure Rate	581,400 DHRs*	0	0.7	170	9 FITs

* EFR data is based on QTP 082703 only, LFR data is based on both QTP 071304, 082704, and 082703 data

¹ Assuming an ambient temperature of 55°C and a junction temperature rise of 15°C.

² Chi-squared 60% estimations used to calculate the failure rate.

³ Thermal Acceleration Factor is calculated from the Arrhenius equation

$$AF = \exp \left[\frac{E_A}{k} \left[\frac{1}{T_2} - \frac{1}{T_1} \right] \right]$$

where:

E_A = The Activation Energy of the defect mechanism.

k = Boltzmann's constant = 8.62x10⁻⁵ eV/Kelvin.

T₁ is the junction temperature of the device under stress and T₂ is the junction temperature of the device at use conditions.

Reliability Test Data

QTP #071304

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 150C, 2.7V, Vcc Max							
CY14B104L (7C14104AC)	4811240	610819876	CML-R	48	1222	0	
CY14B104L (7C14104AC)	4814841	610832326	CML-R	48	1316	0	
CY14B104L (7C14104AC)	4817306	610830615	CML-R	48	932	0	
CY14B104L (7C14104AC)	4819437	610842294	CML-R	48	813	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE, 150C, 2.7V, Vcc Max							
CY14B104L (7C14104AC)	4811240	610819876	CML-R	500	120	0	
CY14B104L (7C14104AC)	4814841	610832326	CML-R	500	120	0	
CY14B104L (7C14104AC)	4817306	610830615	CML-R	500	119	0	
CY14B104L (7C14104AC)	4819437	610842294	CML-R	500	119	0	
STRESS: Pre-/ Post HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE CHAR							
CY14B104L (7C14104AC)	4811240	610819876	CML-R	80/500	10	0	
CY14B104L (7C14104AC)	4814841	610832326	CML-R	80/500	10	0	
CY14B104L (7C14104AC)	4817306	610830615	CML-R	80/500	10	0	
CY14B104L (7C14104AC)	4819437	610842294	CML-R	80/500	10	0	
STRESS: ENDURANCE, 200K CYCLES, 90C							
CY14B104L (7C14104AC)	4811240	610819876	CML-R	COMP	80	0	
CY14B104L (7C14104AC)	4817305	610841260	CML-R	COMP	77	0	
CY14B104L (7C14104AC)	4817306	610830615	CML-R	COMP	160	0	
CY14B104L (7C14104AC)	4819437	610842294	CML-R	COMP	80	0	
CY14B104L (7C14104AC)	4817306/4818074		CML-R	COMP	3307	0	
STRESS: DATA RETENTION, 150C							
CY14B104L (7C14104AC)	4817306	610830615	CML-R	1000	77	0	
CY14B104L (WAFER)	4817306	610830615	CML-R	1008	228	0	
CY14B104L (7C14104AC)	4817305	610841260	CML-R	1000	80	0	
CY14B104L (WAFER)	4817305	610841260	CML-R	1008	216	0	
CY14B104L (7C14104AC)	4818074	N/A	CML-R	1000	80	0	
CY14B104L (WAFER)	4818074	N/A	CML-R	1008	402	0	

Reliability Test Data

QTP # 071304

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: ESD-HUMAN BODY CIRCUIT PER JEDEC EIA/JESD22-A114-B, 2,200V							
CY14B104L (7C14104AC)	4807004	610812949	CML-R	COMP	8	0	
CY14B104L (7C14104AC)	4817306	610830615	CML-R	COMP	8	0	
CY14B104L (7C14104AC)	4811240	610819876	CML-R	COMP	8	0	
STRESS: ESD-CHARGE DEVICE MODEL, 500V							
CY14B104L (7C14104AC)	4807004	610812949	CML-R	COMP	9	0	
CY14B104L (7C14104AC)	4817306	610830615	CML-R	COMP	9	0	
CY14B104L (7C14104AC)	4811240	610819876	CML-R	COMP	9	0	
STRESS: ESD-MACHINE MODEL, 200V							
CY14B104L (7C14104AC)	4807004	610812949	CML-R	COMP	5	0	
CY14B104L (7C14104AC)	4817306	610830615	CML-R	COMP	5	0	
CY14B104L (7C14104AC)	4811240	610819876	CML-R	COMP	5	0	
STRESS: HI-ACCEL SATURATION TEST, 130C, 85%RH, 1.98V, PRE COND 192 HR 30C/60%RH, MSL3							
CY14B104L (7C14104AC)	4811240	610819876	CML-R	128	77	0	
CY14B104L (7C14104AC)	4814841	610832326	CML-R	128	80	0	
CY14B104L (7C14104AC)	4817306	610830615	CML-R	128	77	0	
STRESS: PRESSURE COOKER TEST, 121C, 100%RH, 15 Psig, PRE COND 192 HR 30C/60%RH, MSL3							
CY14B104L (7C14104AC)	4807004	610812949	CML-R	168	77	0	
CY14B104L (7C14104AC)	4814841	610832326	CML-R	168	80	0	
CY14B104L (7C14104AC)	4817306	610830615	CML-R	168	77	0	
STRESS: Temperature Cycle COND. C, -65C TO 150C, PRE COND 192 HRS 30C/60%RH, MSL3							
CY14B104L (7C14104AC)	4807004	610812949	CML-R	1000	77	0	
CY14B104L (7C14104AC)	4817306	610830615	CML-R	1000	80	0	
CY14B104L (7C14104AC)	4814841	610832326	CML-R	500	80	0	
STRESS: STATIC LATCH-UP TESTING, 125C, 5.4V, ±200mA							
CY14B104L (7C14104AC)	4807004	610812949	CML-R	COMP	6	0	
CY14B104L (7C14104AC)	4814841	610832326	CML-R	COMP	6	0	
CY14B104L (7C14104AC)	4819437	610842294	CML-R	COMP	6	0	

Reliability Test Data

QTP # 071304

<i>Device</i>	<i>Fab Lot #</i>	<i>Assy Lot #</i>	<i>Assy Loc</i>	<i>Duration</i>	<i>Samp</i>	<i>Rej</i>	<i>Failure Mechanism</i>
STRESS: AGE BOND							
CY14B104L (7C14104AC)	4807004	610812949	CML-R	COMP	10	0	
CY14B104L (7C14104AC)	4817306	610830615	CML-R	COMP	10	0	
CY14B104L (WAFER)	4818074	N/A	CML-R	COMP	10	0	
STRESS: ACOUSTIC-MSL3							
CY14B104L (7C14104AC)	4807004	610812949	CML-R	COMP	15	0	
CY14B104L (7C14104AC)	4817306	610830615	CML-R	COMP	15	0	
CY14B104L (7C14104AC)	4814841	610832326	CML-R	COMP	15	0	
STRESS: SER – ALPHA PARTICLE, 3-TEPM, 3-VOLTAGE, FIT=550 FIT/Mbit @ 85C, Vcc Nom							
CY14B104L (7C14104AC)	4811240	610819876	CML-R	COMP	3	0	
CY14B104L (7C14104AC)	4817306	610830615	CML-R	COMP	3	0	
CY14B104L (7C14104AC)	4819437	610842294	CML-R	COMP	3	0	
STRESS: SER – NEUTRON/PROTON							
CY14B104L (7C14104AC)	4808220	N/A	CML-R	COMP	3	0	
STRESS: LOW TEMPERATURE OPERATING LIFE TEST, -30C, 2.7V, Vcc Max							
CY14B104L (7C14104AC)	4817306	610830615	CML-R	500	77	0	
STRESS: HIGH TEMP STEADY STATE LIFE TEST, 150C, 2.7V, Vcc Max							
CY14B104L (7C14104AC)	4811240	610819876	CML-R	1000	76	0	

Reliability Test Data

QTP #: 082704

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 150C, 2.7V, Vcc Max							
CY14B104K (7C1404B1C)	4847698	610905735	CML-R	48	1787	0	
CY14B104NA (7C1404B6C)	4850719	610910241	CML-R	48	1774	0	
CY14B104NA (7C1404B6C)	4850719	610914474	CML-R	48	1555	1	1-unfilled via, FA#082704-3CE1 CAR#200930051
CY14B104K (7C1404B1C)	4906080	610918905	CML-R	48	1136	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE, 150C, 2.7V, Vcc Max							
CY14B104K (7C1404B1C)	4847698	610905735	CML-R	500	118	0	
CY14B104NA (7C1404B6C)	4850719	610910241	CML-R	500	147	0	
CY14B104NA (7C1404B6C)	4850719	610914474	CML-R	500	186	0	
CY14B104K (7C1404B1C)	4906080	610918905	CML-R	500	119	0	
STRESS: Pre-/ Post HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE CHAR							
CY14B104K (7C1404B1C)	4847698	610905735	CML-R	80/500	10	0	
CY14B104NA (7C1404B6C)	4850719	610910241	CML-R	80/500	10	0	
STRESS: ENDURANCE (90C), 200K CYCLES+168 HOURS DATA RETENTION							
CY14B104K (7C1404B1C)	4847698	610904566	CML-R	COMP	80	0	
CY14B104NA (7C1404B6C)	4850719	610910241	CML-R	COMP	89	0	
STRESS: DATA RETENTION (150C) + 200K ENDURANCE							
CY14B104K (7C1404B1C)	4847698	610904566	CML-R	1000	80	0	
CY14B104NA (7C1404B6C)	4850719	610910241	CML-R	1000	80	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER JEDEC EIA/JESD22-A114-B, 2,200V							
CY14B104K (7C1404B1C)	4847698	610904566	CML-R	COMP	8	0	
CY14B104NA (7C1404B6C)	4850719	610910241	CML-R	COMP	8	0	
CY14E104KA (7C1404E1C)	4850719	610910242	CML-R	COMP	8	0	
CY14B104K (7C1404B1C)	4906080	610918905	CML-R	COMP	8	0	
STRESS: ESD-CHARGE DEVICE MODEL, 500V							
CY14B104K (7C1404B1C)	4847698	610904566	CML-R	COMP	9	0	
CY14B104LA (7C1404B8C)	4847698	610914510	G	COMP	9	0	
CY14B104NA (7C1404B7C)	4847698	610918518	G	COMP	9	0	

Reliability Test Data

QTP #: 082704

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: ESD-MACHINE MODEL, 200V							
CY14B104K (7C1404B1C)	4847698	610904566	CML-R	COMP	5	0	
STRESS: HI-ACCEL SATURATION TEST, 130C, 85%RH, 1.98V, PRE COND 192 HR 30C/60%RH, MSL3							
CY14B104K (7C1404B1C)	4847698	610904566	CML-R	128	80	0	
STRESS: PRESSURE COOKER TEST, 121C, 100%RH, 15 Psig, PRE COND 192 HR 30C/60%RH, MSL3							
CY14B104K (7C1404B1C)	4847698	610904566	CML-R	168	77	0	
STRESS: TEMPERATURE CYCLE COND. C, -65C TO 150C, PRE COND 192 HRS 30C/60%RH, MSL3							
CY14B104K (7C1404B1C)	4847698	610904566	CML-R	1000	75	0	
CY14B104K (7C1404B1C)	4841954	610855137	CML-R	1000	77	0	
STRESS: STATIC LATCH-UP TESTING, 125C, 5.4V, ±200mA							
CY14B104K (7C1404B1C)	4847698	610904566	CML-R	COMP	9	0	
CY14B104NA (7C1404B6C)	4850719	610910241	CML-R	COMP	9	0	
CY14E104KA (7C1404E1C)	4850719	610910242	CML-R	COMP	9	0	
CY14B104K (7C1404B1C)	4906080	610918905	CML-R	COMP	9	0	
STRESS: ACOUSTIC-MSL3							
CY14B104K (7C1404B1C)	4847698	610904566	CML-R	COMP	15	0	
CY14B104K (7C1404B1C)	4841954	610855137	CML-R	COMP	15	0	
STRESS: SER – ALPHA PARTICLE, 3-TEPM, 3-VOLTAGE, @ 85C, Vcc Nom							
CY14B104NA (7C1404B6C)	4850719	610910241	CML-R	COMP	3	0	



Reliability Test Data

QTP #: 092804

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: ENDURANCE (90C) 1 MILLION CYCLES+168 HOURS DATA RETENTION							
CY14B104NA (7C1404B6C)	4850719	610910241	CML-R	COMP	80	0	
CY14B104LA (7C1404B8C)	4919815	610923434	CML-R	COMP	80	0	
STRESS: ENDURANCE (24C) 1 MILLION CYCLES+168 HOURS DATA RETENTION							
CY14B104K (7C1404B1C)	4847698	610905735	CML-R	COMP	79	0	



Reliability Test Data

QTP #: 082703

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: ACOUSTIC, MSL3							
CY14B108L (7C1408B8B)	4847673	610907084	TWN-G	COMP	15	0	
CY14B108L (7C1408B8B)	4839870	610904599	TWN-G	COMP	15	0	
CY14B108L (7C1408B8B)	4844914	610916942	TWN-G	COMP	15	0	
STRESS: CLASSYIELD							
CY14B108L (7C1408B8B)	4844914	610916942	TWN-G	COMPARABLE			
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	COMPARABLE			
STRESS: DATA RETENTION, 150C							
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	500	77	0	
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	1000	77	0	
STRESS: E-TEST							
7C1408B8BC	4844914	610916942	TWN-G	COMPARABLE			
7C1408B1C	4910266	610916943	TWN-G	COMPARABLE			
STRESS: ENDURANCE							
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	168	77	0	
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	500	77	0	
STRESS: ESD-CHARGE DEVICE MODEL, 500V							
CY14B108L (7C1408B8B)	4847673	610907084	TWN-G	COMP	9	0	
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	COMP	9	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER JEDEC EIA/JESD22-A114-B, 2,200V							
CY14B108L (7C1408B8B)	4847673	610907084	TWN-G	COMP	8	0	
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	COMP	8	0	
STRESS: ESD-MACHINE MODEL, 200V							
CY14B108L (7C1408B8B)	4847673	610907084	TWN-G	COMP	5	0	
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	COMP	5	0	
STRESS: HI-ACCEL SATURATION TEST, 130C, 85%RH, 3.3V, PRE COND 192 HR 30C/60%RH, MSL3							
CY14B108L (7C1408B8B)	4847673	610907084	TWN-G	128	80	0	
CY14B108L (7C1408B8B)	4844914	610916942	TWN-G	128	45	0	



Reliability Test Data

QTP #: 082703

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 150C, 2..1V, Vcc Max							
CY14B108L (7C1408B8B)	4844914	610916942	TWN-G	48	324	0	
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	48	1234	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE, 150C, 2.1V, Vcc Max							
CY14B108L (7C1408B8B)	4844914	610916942	TWN-G	80	119	0	
CY14B108L (7C1408B8BC)	4844914	610916942	TWN-G	500	114	0	
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	80	240	0	
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	500	240	0	
STRESS: PRESSURE COOKER TEST, 121C, 100%RH, 15 Psig, PRE COND 192 HR 30C/60%RH, MSL3							
CY14B108L (7C1408B8B)	4847673	610907084	TWN-G	168	80	0	
CY14B108L (7C1408B8B)	4847673	610907084	TWN-G	288	80	0	
CY14B108L (7C1408B8B)	4844914	610916942	TWN-G	168	45	0	
CY14B108L (7C1408B8B)	4844914	610916942	TWN-G	288	43	0	
STRESS: Pre-/ Post HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE CHAR							
CY14B108L (7C1408B8B)	4844914	610916942	TWN-G	COMP	12	0	
STRESS: STATIC LATCH-UP TESTING, 125C, 5.4V, ±200mA							
CY14B108L (7C1408B8B)	4847673	610907084	TWN-G	COMP	6	0	
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	COMP	6	0	
STRESS: SORT YIELD							
CY14B108L (7C1408B8B)	4844914	610916942	TWN-G	COMPARABLE			
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	COMPARABLE			
STRESS: TEMPERATURE CYCLE COND. C, -65C TO 150C, PRE COND 192 HRS 30C/60%RH, MSL3							
CY14B108L (7C1408B8B)	4847673	610907084	TWN-G	500	80	0	
CY14B108L (7C1408B8B)	4847673	610907084	TWN-G	1000	80	0	
CY14B108L (7C1408B8B)	4839870	610904599	TWN-G	500	77	0	
CY14B108L (7C1408B8B)	4839870	610904599	TWN-G	1000	77	0	
CY14B108L (7C1408B8B)	4844914	610916942	TWN-G	500	77	0	
CY14B108L (7C1408B8B)	4844914	610916942	TWN-G	1000	77	0	
STRESS: THERMAL JUNCTION							
CY14B108K (7C1408B1C)	4910266	610916943	TWN-G	COMP	5	0	

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Document History Page

Document Title: QTP 082703: 8MEG NVSRAM PRODUCT FAMILY S8TNV-5, FAB 4
Document Number: 001-85728

Rev.	ECN No.	Orig. of Change	Description of Change
**	3873723	NSR	Initial Spec Release
*A	4633062	HSTO	Align qualification report based on the new template in the front page

Distribution: WEB

Posting: None